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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SK2955

Silicon N Channel MOS FET
High Speed Power Switching

RENESAS

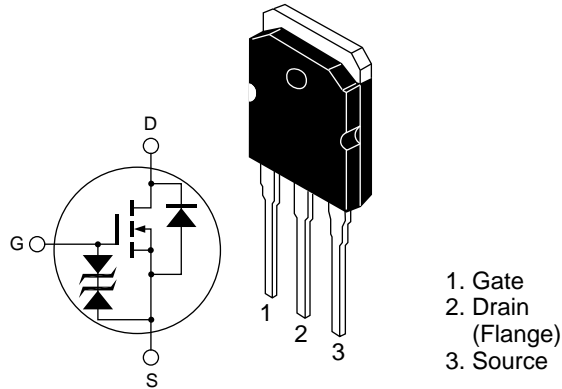
ADE-208-564B (Z)
3rd. Edition
Jul. 1998

Features

- Low on-resistance
 $R_{DS} = 0.010 \Omega$ typ.
- High speed switching
- 4V gate drive device can be driven from 5V source

Outline

TO-3P



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	45	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	180	A
Body-drain diode reverse drain current	I_{DR}	45	A
Avalanche current	I_{AP} ^{Note3}	45	A
Avalanche energy	E_{AR} ^{Note3}	173	mJ
Channel dissipation	Pch ^{Note2}	100	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

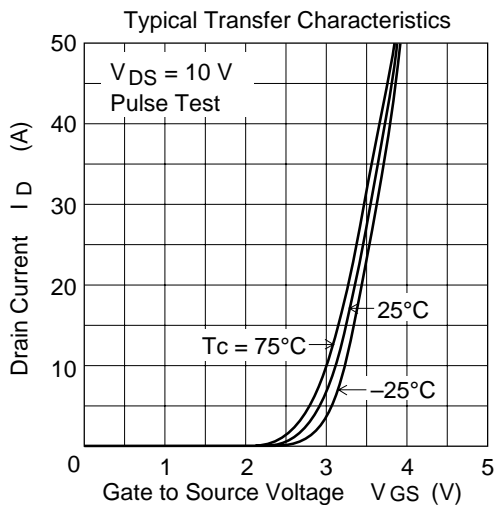
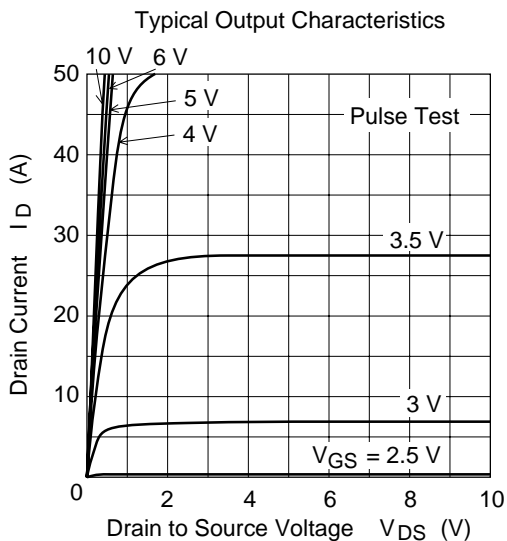
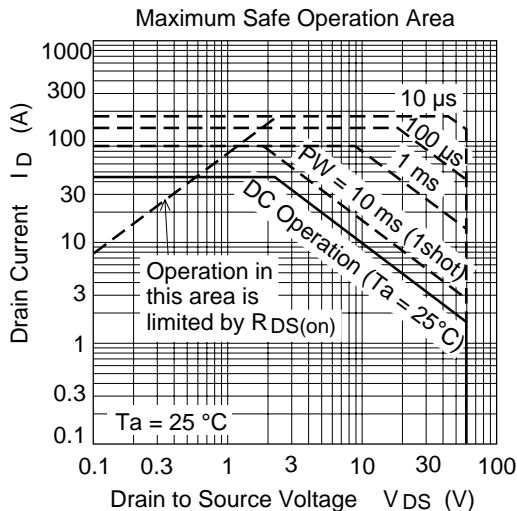
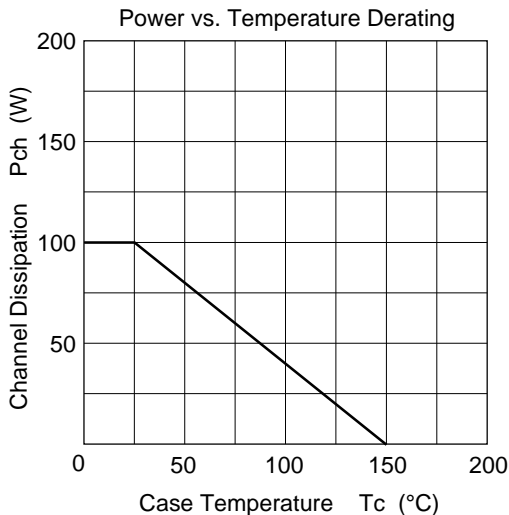
Note: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$
 2. Value at $T_c = 25^\circ C$
 3. Value at $T_{ch} = 25^\circ C$, $R_g = 50\Omega$

Electrical Characteristics (Ta = 25°C)

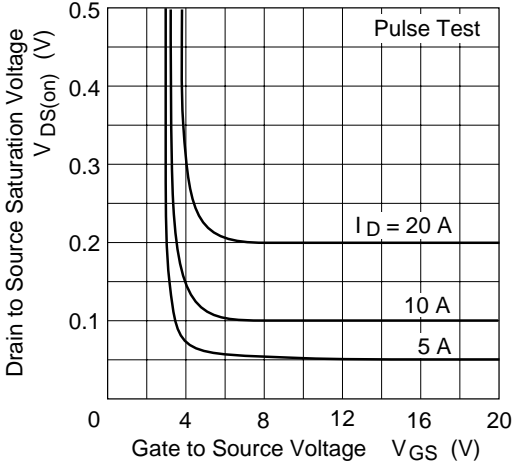
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10mA, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100\mu A, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16V, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 60V, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	—	2.5	V	$I_D = 1mA, V_{DS} = 10V$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.010	0.013	Ω	$I_D = 20A, V_{GS} = 10V$ ^{Note4}
	$R_{DS(on)}$	—	0.015	0.025	Ω	$I_D = 20A, V_{GS} = 4V$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	24	40	—	S	$I_D = 20A, V_{DS} = 10V$ ^{Note4}
Input capacitance	C_{iss}	—	2200	—	pF	$V_{DS} = 10V$
Output capacitance	C_{oss}	—	1050	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	320	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	25	—	ns	$I_D = 20A, V_{GS} = 10V$
Rise time	t_r	—	200	—	ns	$R_L = 1.5\Omega$
Turn-off delay time	$t_{d(off)}$	—	320	—	ns	
Fall time	t_f	—	240	—	ns	
Body-drain diode forward voltage	V_{DF}	—	0.95	—	V	$I_F = 45A, V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	60	—	ns	$I_F = 45A, V_{GS} = 0$ $diF/dt = 50A/\mu s$

Note: 4. Pulse test

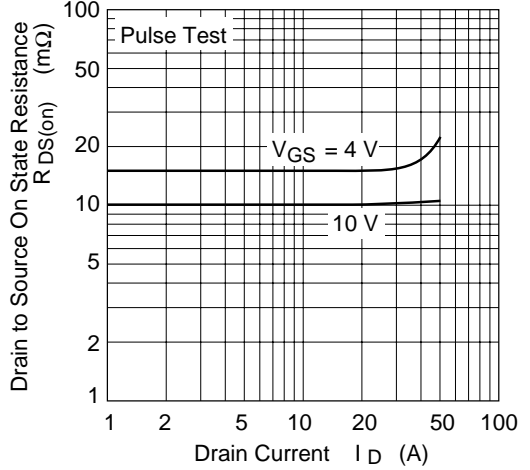
Main Characteristics



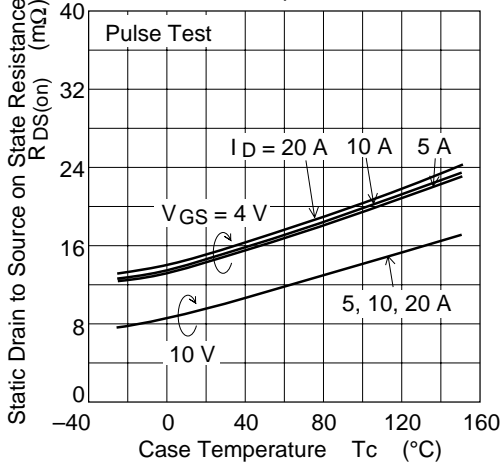
Drain to Source Saturation Voltage vs. Gate to Source Voltage



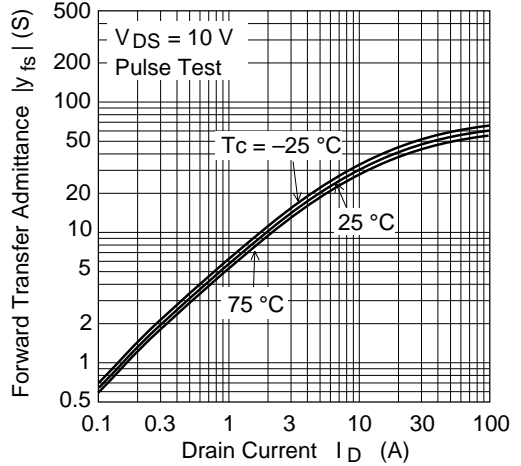
Static Drain to Source on State Resistance vs. Drain Current

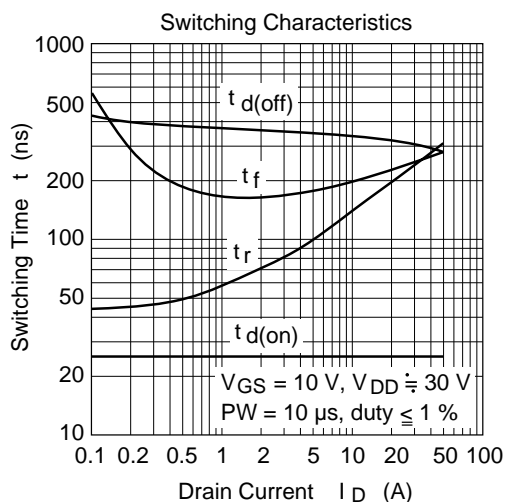
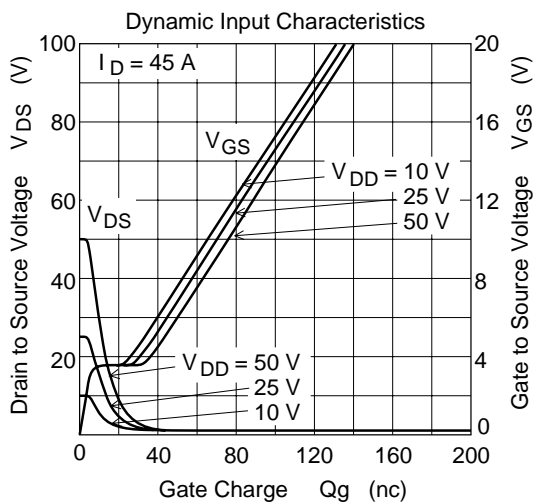
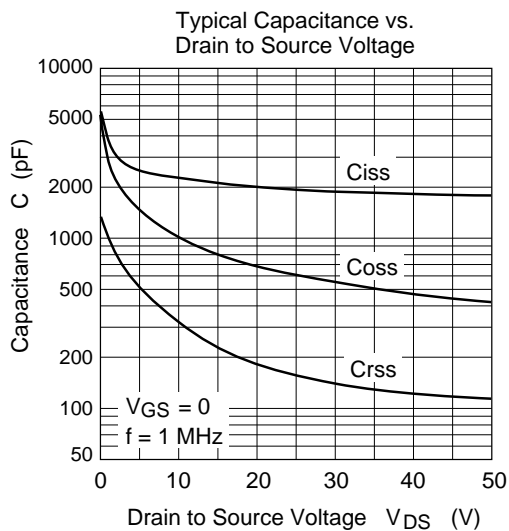
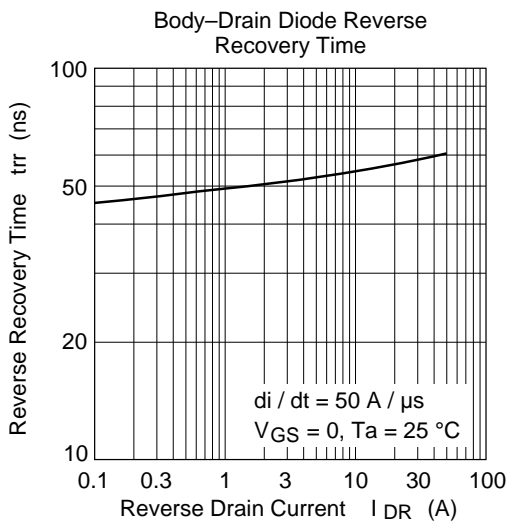


Static Drain to Source on State Resistance vs. Temperature

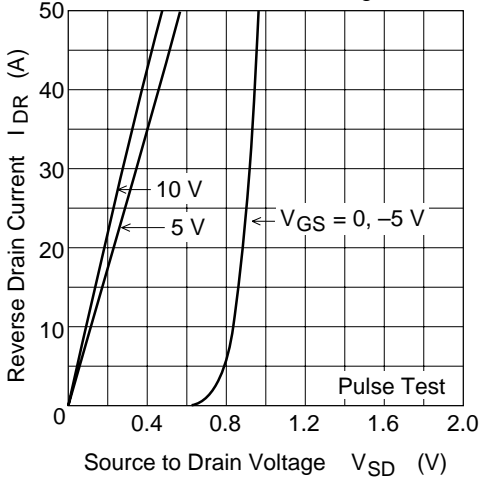


Forward Transfer Admittance vs. Drain Current

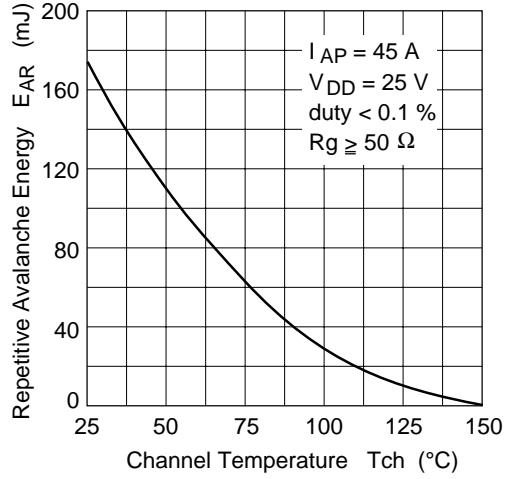




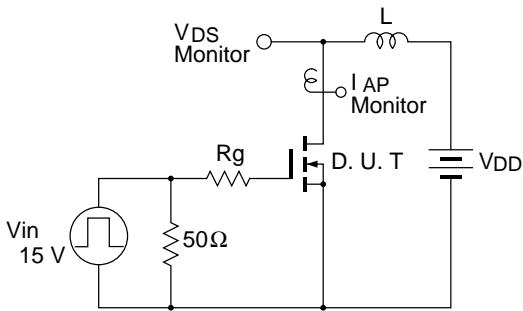
Reverse Drain Current vs. Source to Drain Voltage



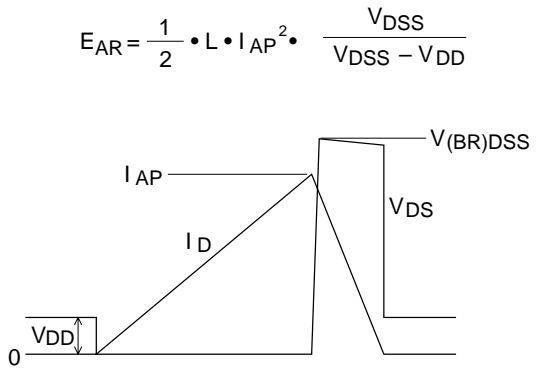
Maximum Avalanche Energy vs. Channel Temperature Derating



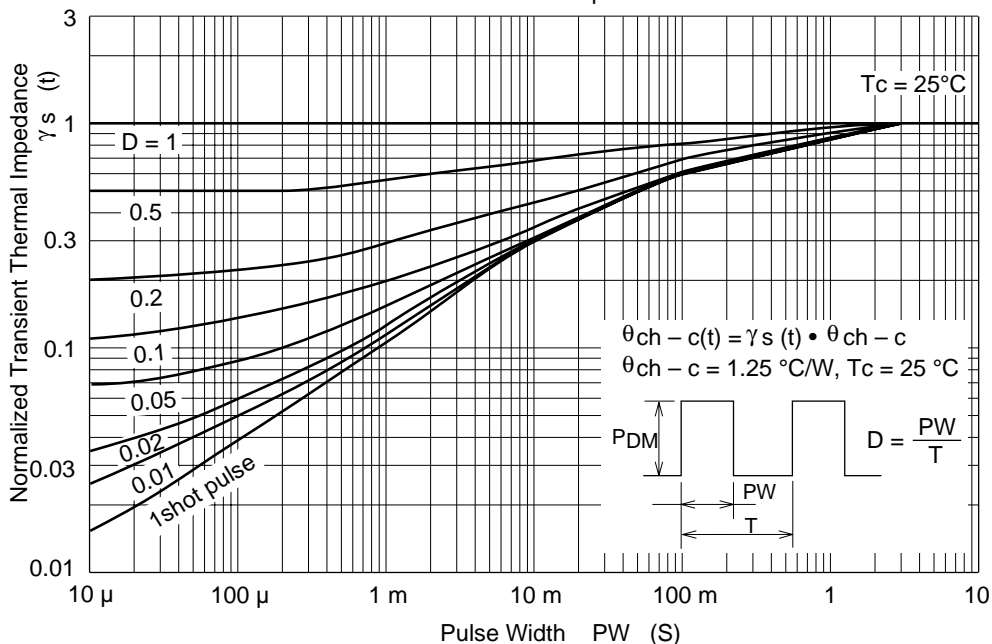
Avalanche Test Circuit



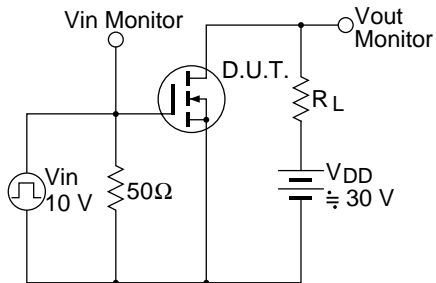
Avalanche Waveform



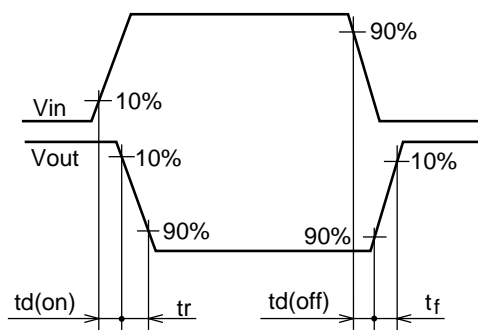
Normalized Transient Thermal Impedance vs. Pulse Width



Switching Time Test Circuit



Waveform



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